Amendments to the Title

Please change the title to the following: --METHODS OF FORMING TRENCH ISOLATION REGIONS--.

Am ndm nts to the Specification

At page 1 before the "Technical Field" section, please insert the following:

--RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 10/330,881, filed December 23, 2002, entitled "Method of Forming Trench Isolation Regions", naming Trung Tri Doan and Gurtej S. Sandhu as inventors, the disclosure of which is incorporated by reference; which was a continuation application of U.S. Patent Application Serial No. 10/209,865, filed August 2, 2002, entitled "Method of Forming Trench Isolation Regions", naming Trung Tri Doan and Gurtej S. Sandhu as inventors, now U.S. Patent No. 6,583,028, the disclosure of which is incorporated by reference; which was a continuation application of U.S. Patent Application Serial No. 09/900,117, filed July 6, 2001, entitled "Method of Forming Trench Isolation Regions", naming Trung Tri Doan and Gurtej S. Sandhu as inventors, the disclosure of which is incorporated by reference; which was a continuation of U.S. Patent Application Serial No. 09/385,915, filed on August 30, 1999, entitled "Method of Forming Trench Isolation Regions", naming Trung Tri Doan and Gurtej S. Sandhu as inventors, now U.S. Patent

No. 6,300,219 B1, the disclosure of which is incorporated by reference.--

Please amend the paragraph beginning at line 16 on page 4 as follows:

Figure 3 is a view of the Figure 1 substrate fragment at a processing step subsequent to that shown in ~~of~~ Figure 2.

Please amend the paragraph beginning at line 18 on page 4 as follows:

Figure 4 is a view of the Figure 1 substrate fragment at a processing step subsequent to that shown in ~~of~~ Figure 3.

Please amend the paragraph beginning at line 18 on page 13 as follows:

Further in accordance with the invention, sidewalls 16 might be oxidized prior to forming first layer 26 in the first embodiment, or prior to forming first layer 40 in the second embodiment. Alternately, sidewalls 16 might be oxidized after forming first layer 26 and before forming second layer 30 in the first embodiment, or after forming first layer 40 and before forming second layer 44 in the second ~~embodiment~~ embodiment, or after forming layer 50 and before forming layer 30 in the third embodiment. Further alternately, sidewalls 16 might be oxidized after forming second layer 30 in the first embodiment, or after forming layer 44 in the second embodiment. Further alternately with respect to the third embodiment, and where layer 21 is not formed by thermal oxidation, the sidewalls might be oxidized after forming layer 50 and before forming layer 30, or after forming layer 50. Conventional thermal oxidations are preferably conducted in such instances.